# 2SB0947 (2SB947), 2SB0947A (2SB947A)

## Silicon PNP epitaxial planar type

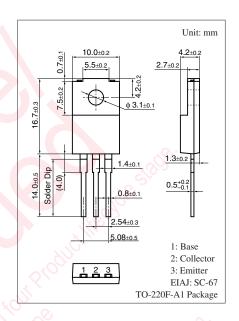
### For low-voltage switcing

#### ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0947	V <sub>CBO</sub>	-40	V
(Emitter open)	2SB0947A		-50	
Collector-emitter voltage	2SB0947	V <sub>CEO</sub>	-20	V
(Base open)	2SB0947A		-40	
Emitter-base voltage (Coll	V <sub>EBO</sub>	-5	V	
Collector current	$I_{C}$	-10	A	
Peak collector current	$I_{CP}$	-15	A	
Collector power	$P_{C}$	35	W	
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	



## ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SB0947	$V_{CEO}$	$I_C = -10 \text{ mA}, I_B = 0$	-20	10	. (	V
(Base open)	2SB0947A			-40	0///		
Collector-base cutoff	2SB0947	$I_{CBO}$	$V_{CB} = -40 \text{ V}, I_{E} = 0$	2.	5	-50	μΑ
current (Emitter open)	2SB0947A		$V_{CB} = -50 \text{ V}, I_E = 0$	0,0,		-50	
Emitter-base cutoff current (Collector open)		$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-50	μΑ
Forward current transfer rat	Forward current transfer ratio		$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$	45			_
	91,	h <sub>FE2</sub> *	$V_{CE} = -2 \text{ V}, I_C = -2 \text{ A}$	60		260	
Collector-emitter saturation	voltage	V <sub>CE(sat)</sub>	$I_C = -7 \text{ A}, I_B = -0.23 \text{ A}$			- 0.6	V
Base-emitter saturation voltage		V <sub>BE(sat)</sub>	$I_C = -7 \text{ A}, I_B = -0.23 \text{ A}$			-1.5	V
Transition frequency		$f_T$	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}, f = 10 \text{ MHz}$		150		MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		200		pF
(Common base, input open circuited)							
Turn-on time		t <sub>on</sub>	$I_C = -2 \text{ A}, I_{B1} = -66 \text{ mA}, I_{B2} = 66 \text{ mA}$		0.1		μs
Storage time		t <sub>stg</sub>	$V_{CC} = -20 \text{ V}$		0.5		μs
Fall time		$t_{\mathrm{f}}$			0.1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

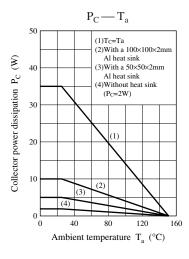
#### 2. \*: Rank classification

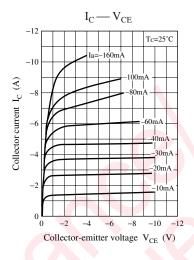
Rank	R	Q	Р	
$h_{\rm FE2}$	60 to 120	90 to 180	130 to 260	

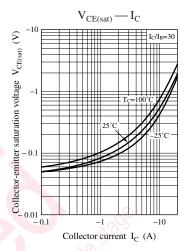
Note) The part numbers in the parenthesis show conventional part number.

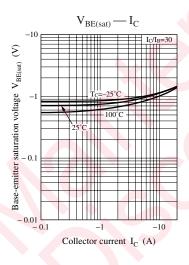
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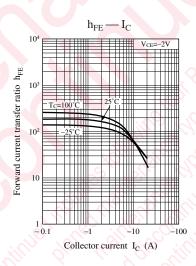
## **Panasonic**

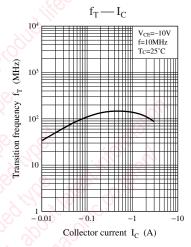


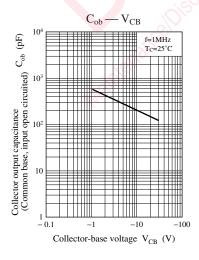


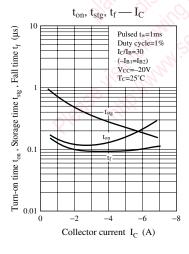


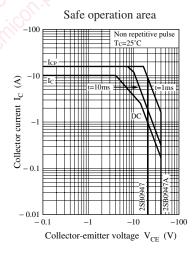




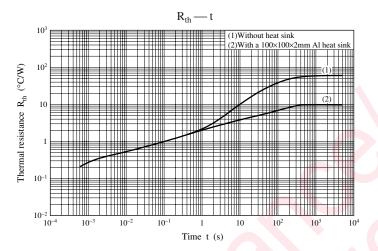








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